

Preliminary Specification

RCL Semiconductors Ltd.



Tri-State Octal D-Type Flip-Flops (Edge Triggered)

HC374

GENERAL DESCRIPTION

HC374 is fabricated in the high-speed silicon gate CMOS technology. It has the high noise immunity and low power consumption of standard CMOS integrated circuits. It also offers speeds comparable to low power Schottky devices (LS-TTL).

These 8-bit flip-flops with 3-state outputs are specifically designed for driving highly capacitive or relatively low-impedance loads. They are particularly suitable for implementing buffer registers, I/O ports, bi-directional bus drivers, and working registers.

HC374 has octal positive edge triggered D-type flip-flops. On the positive transition of the clock (CK) input, data at the inputs D, meeting the setup and hold time requirement, are transferred to the Q outputs.

An output-enable input (\overline{OE}) places the eight outputs in either a normal logic state (H or L logic levels) or the high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and increased drive provide the capability to drive bus lines without interface or pull-up components.

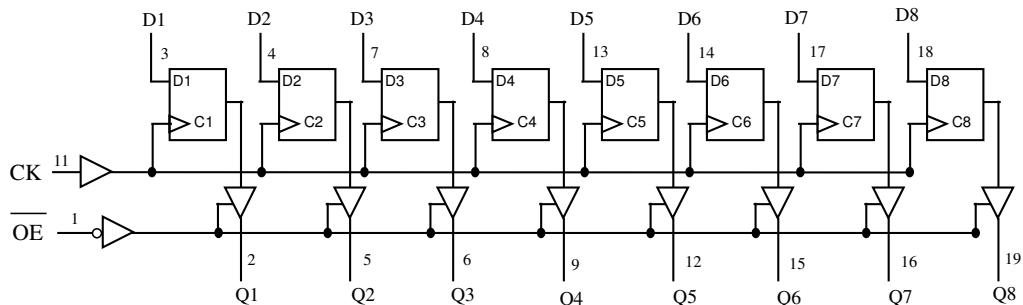
\overline{OE} does not affect the internal operation of the flip-flops. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

\overline{OE} should be tied to VDD through a pull-up resistor to ensure the high-impedance state during power up or power down; the minimum value of the resistor is determined by the current-sinking capability of the driver.

FEATURES

- Wide operating supply voltage range: 2-6V
- Output Drive at $VDD = 5V : \pm 6mA$
- Typical propagation delay: 14ns
- Low input current: $< 1\mu A$
- Low quiescent supply current: $80\mu A$ maximum
- Octal D-type flip-flops in a single package
- Full Parallel access for Loading

LOGIC DIAGRAM



FUNCTIONAL DESCRIPTION**Truth Table**

Inputs			Outputs
OE	CK	D	Q
L	↑	H	H
L	↑	L	L
L	H or L	X	Q ₀
H	X	X	Z

H = High Level (steady state). L= Low Level (steady state)

X = Irrelevant (any input, including transitions)

↑ = Transition from low to high level.

Z = high impedance state

Q₀= The level of the output before steady state input conditions were established**ABSOLUTE MAXIMUM RATINGS**

Parameter	Value	Unit
DC supply voltage (VDD)	- 0.5 ~ + 7.0	V
DC input or output Voltage (V _{IN} , V _{OUT})	-0.5 to VDD +0.5	V
DC Current Drain per pin, any output (I _{out})	±35	mA
DC Current Drain per pin, VDD or GND (I _{cc})	±70	mA
Storage Temperature(T _{STG})	-65 ~ +150	°C

Note: 1. Absolute maximum ratings are those values beyond which the safety of the device cannot be guaranteed.

RECOMMENDED OPERATING CONDITIONS

Parameter	Min.	Normal	Max.	Unit
DC Supply Voltage (VDD)	2.0	5.0	6.0	V
VIH High-level Input Voltage	VDD=2.0V VDD=4.5V VDD=6.0V	1.5 3.15 4.2		V
VIL Low-level Input Voltage	VDD=2.0V VDD=4.5V VDD=6.0V		0.5 1.35 1.8	V
VI Input Voltage		0	VDD	V
VO Output Voltage		0	VDD	V
Operating Temperature (TA)	74HC374 54HC374	-40 -55	+85 +125	°C
Input Rise/Fall Times (tr, tf)	VDD=2.0V VDD=4.5V VDD=6.0V		1000 500 400	ns

Note: 2. All unused inputs of the device must be held at VDD or GND to ensure proper device operation.

DC ELECTRICAL CHARACTERISTICS

(unless otherwise specified)

Parameter	Test Conditions	VDD	TA =25 °C			54HC374		74HC374		Unit	
			Min.	Typ.	Max.	Min.	Max.	Min.	Max.		
VOH	VI=VIH or VIL	IOH= -20µA	2.0V	1.9	1.998	1.9		1.9		V	
			4.5V	4.4	4.499	4.4		4.4			
			6.0V	5.9	5.999	5.9		5.9			
		IOH= -6mA	4.5V	3.98	4.3	3.7		3.84		V	
			6.0V	5.48	5.8	5.2		5.34			
		IOL = 20µA	2.0V		0.002	0.1		0.1		V	
			4.5V		0.001	0.1		0.1			
			6.0V		0.001	0.1		0.1			
			4.5V		0.17	0.26		0.4			
		IOL = 7.8mA	6.0V		0.15	0.26		0.4			
I _l	VI=VDD or 0		6.0V		±0.1	±100		±1000		nA	
I _{OZ}	VO =VDD or 0		6.0V		±0.01	±0.5		±10		µA	
I _{CC}	VI=VDD or 0	IO =0	6.0V			8		160		80	µA
C _i			2~6V		3	10		10		10	pF

TIMING REQUIREMENTS OVER RECOMMENDED OPERATING TEMPERATURE RANGE
 (unless otherwise noted)

Parameter	VDD	TA =25 °C		54HC374		74HC374		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	
f _{CLOCK}	Clock frequency	2.0V	6		4		5	MHz
		4.5V	30		20		24	
		6.0V	35		24		28	
t _w	Pulse duration, CK high or low	2.0V	80		120		100	ns
		4.5V	16		24		20	
		6.0V	14		20		17	
t _{su}	Setup time, data before CK↑	2.0V	100		150		125	ns
		4.5V	20		30		25	
		6.0V	17		25		21	
t _h	Hold time, data after CK↑	2.0V	10		13		12	ns
		4.5V	5		5		5	
		6.0V	5		5		5	

AC ELECTRICAL CHARACTERISTICS (CL = 50pF)

Parameter	From (Input)	To (Output)	VDD	TA =25 °C			54HC374	74HC374	Unit
				Min.	Typ.	Max	Min.	Max.	
f_{max}			2.0V	6	12		4	5	MHz
			4.5V	30	60		20	24	
			6.0V	35	70		24	28	
t_{pd}	CK	Any Q	2.0V		63	180	270	225	ns
			4.5V		17	36	54	45	
			6.0V		15	31	46	38	
t_{en}	\overline{OE}	Any Q	2.0V		60	150	225	190	ns
			4.5V		16	30	45	38	
			6.0V		14	26	38	32	
t_{dis}	\overline{OE}	Any Q	2.0V		36	150	225	190	ns
			4.5V		17	30	45	38	
			6.0V		16	26	38	32	
t_t		Any Q	2.0V		28	60	90	75	ns
			4.5V		8	12	18	15	
			6.0V		6	10	15	13	

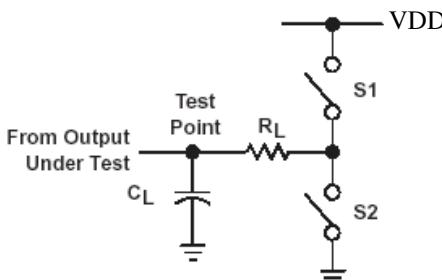
AC ELECTRICAL CHARACTERISTICS (CL = 150pF)

Parameter	From (Input)	To (Output)	VDD	TA =25 °C			54HC374	74HC374	Unit
				Min.	Typ.	Max	Min.	Max.	
f_{max}			2.0V	6	12			5	MHz
			4.5V	30	60			24	
			6.0V	35	70			28	
t_{pd}	CK	Any Q	2.0V		80	230	345	290	ns
			4.5V		22	46	69	58	
			6.0V		19	39	58	49	
t_{en}	\overline{OE}	Any Q	2.0V		70	200	300	250	ns
			4.5V		25	40	60	50	
			6.0V		22	34	51	43	
t_t			2.0V		45	210	315	265	ns
			4.5V		17	42	63	53	
			6.0V		13	36	53	45	

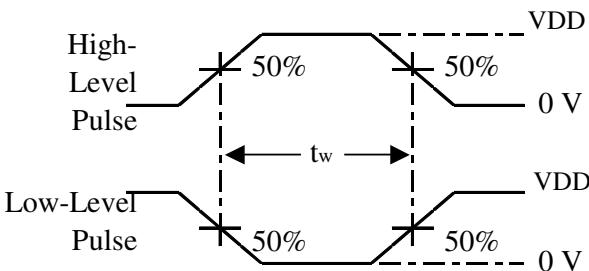
Parameter	Test Conditions	Typ.	Unit
C_{PD} Power Dissipation Capitance	TA =25 °C , No Load	100	pF

Note 3: C_{PD} determines the no load dynamic power consumption , $P_D=C_{PD} \cdot VDD^2 \cdot f + I_{cc} \cdot VDD$, and the no load dynamic current consumption, $I_S = C_{PD} \cdot VDD \cdot f_i + I_{cc}$

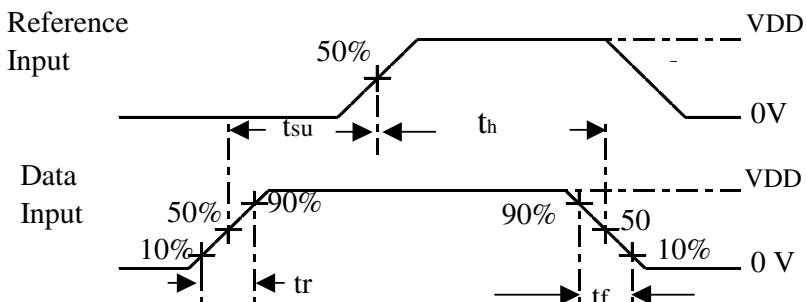
AC TEST CIRCUIT AND AC SWITCHING WAVEFORM



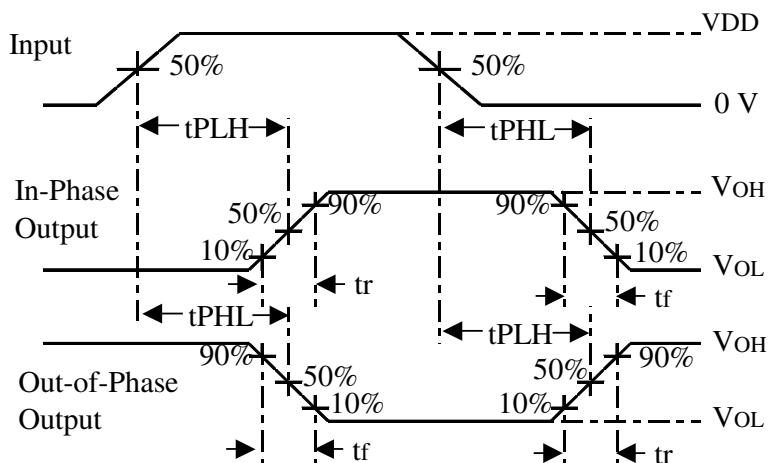
PARAMETER		R _L	C _L	S1	S2
ten	t _{PZH}	1kΩ	50pF	Open	Closed
	t _{PZL}		150pF	Closed	Open
tdis	t _{PHZ}	1kΩ	50pF	Open	Closed
	t _{PLZ}		150pF	Closed	Open
tpd or t _f		---	50pF or 150pF	Open	Open



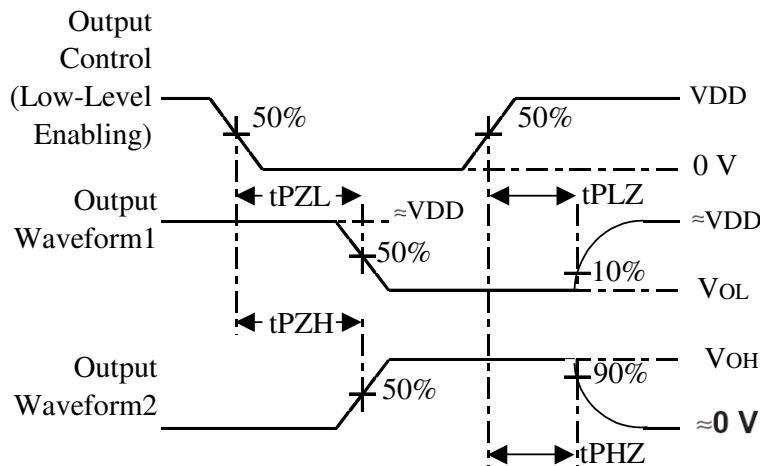
Voltage Waveforms
Pulse Durations



Voltage Waveforms
Setup and Hold and Input rise and Fall times



Voltage Waveforms
Propagation Delay and Output Transition Times

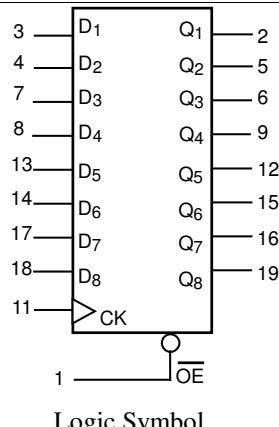
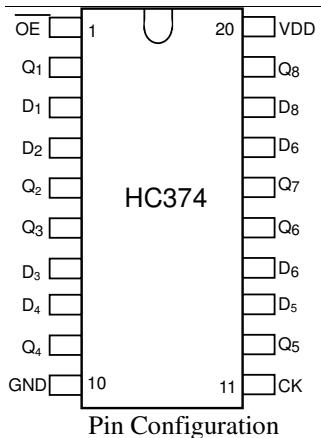


Voltage Waveforms
Enable and disable times for 3-state outputs

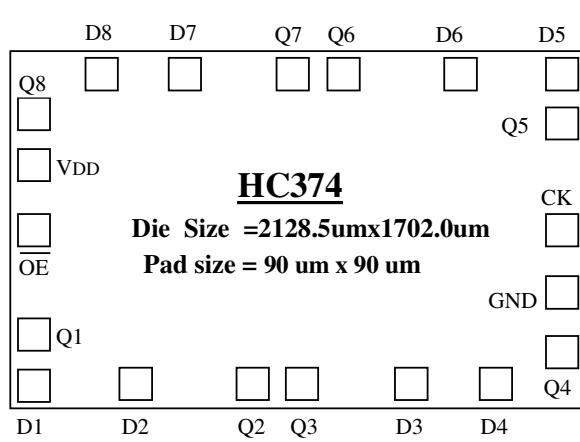
- NOTES 4:**
- 1) C_L includes probe and test-fixture capacitance.
 - 2) Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control.
Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - 3) Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics:
 $\text{PRR } \delta 1 \text{ MHz}, Z_O = 50\Omega, tr = 6 \text{ ns}, tf = 6 \text{ ns}$.
 - 4) For clock inputs, f_{max} is measured when the input duty cycle is 50%.
 - 5) The outputs are measured one at a time with one input transition per measurement.
 - 6) t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - 7) t_{PZL} and t_{PZH} are the same as ten.
 - 8) t_{PLH} and t_{PHL} are the same as t_{pd} .

PIN DESCRIPTION

PIN NO.	SYMBOL	DESCRIPTION
3, 4, 7, 8, 13, 14, 17, 18	D1–D8	Data Inputs
2, 5, 6, 9, 12, 15, 18, 19	Q1 – Q8	Outputs
10	GND	Ground (0V)
11	CK	Clock input (active at rising edge)
1	\overline{OE}	Output Enable
20	VDD	Positive power supply



PAD DIAGRAM



The Coordinate of Each Pad

Q1 (-779.8, -337.8)	Q5 (689.5, 247.7)
D1 (-779.8, -977.7)	D5 (689.5, 387.7)
D2 (-496.0, -977.7)	D6 (405.7, 387.7)
Q2 (-171.0, -977.7)	Q6 (80.7, 387.7)
Q3 (-31.0, -977.7)	Q7 (-59.3, 387.7)
D3 (273.5, -977.7)	D7 (-363.8, 387.7)
D4 (502.3, -977.7)	D8 (-592.6, 387.7)
Q4 (689.5, -385.7)	Q8 (-779.8, 274.1)
GND (689.5, -224.1)	VDD (-779.8, 134.1)
CK (689.5, -45.1)	OE (-779.8, -44.9)

Note: Substrate should be connected to VDD or left it open.

PAD IDENTIFICATION

